

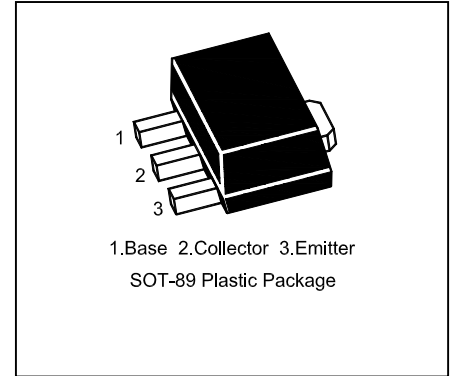
Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURES

Power dissipation

MARKING:P1



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-80	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current –Continuous	-1	A
P _C	Collector Power Dissipation	0.5	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-65~150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-80		V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C = -10mA, I _B =0	-60		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-60 V, I _E =0		-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4 V, I _C =0		-0.1	μA
Collector- Emitter cut-off current	I _{CES}	V _{CE} =-60 V, I _E =0		-0.1	μA
DC current gain	h _{FE} *	V _{CE} =-5V, I _C = -1mA V _{CE} =-5V, I _C = -500mA V _{CE} =-5V, I _C = -1A V _{CE} =-5V, I _C = -2A	100 100 80 15	300	
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =-500 mA, I _B = -50mA I _C =-1A, I _B = -100mA		-0.3 -0.6	V
Base-emitter saturation voltage	V _{BE(sat)} *	I _C =-1A, I _B = -100mA		-1.2	V
Base-emitter voltage	V _{BE} *	V _{CE} =-5V, I _C = -1A		-1	V
Transition frequency	f _T	V _{CE} = -10V, I _C =- 50mA f =100MHz	150		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, f=1MHz		10	pF

*Pulse width=300s. Duty cycle 2%